

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Extended temperature range T_i = 175 °C
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- DC to DC conversion
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{sp} = 25 °C		-	-	26	А
P _{tot}	total power dissipation	T _{sp} = 25 °C		-	-	19	W
Static chara	cteristics		- I				
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 8.5 A; T _j = 25 °C		-	13	16	mΩ

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5. Pinning information

Table 2	Table 2. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol					
1	D	drain		D					
2	D	drain							
3	G	gate		G ↓ ↓ ↓ ↓ ↓					
4	S	source	3 8 4						
5	D	drain	Transparent top view						
6	D	drain	DFN2020MD-6 (SOT1220)	s					
7	D	drain		017aaa255					
8	S	source							

6. Ordering information

Type number	Package					
	Name	Description	Version			
BUK4D16-20		plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1220			

7. Marking

Table 4.	Marking	codes
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Type number	Marking code
BUK4D16-20	6L

20 V, N-channel Trench MOSFET

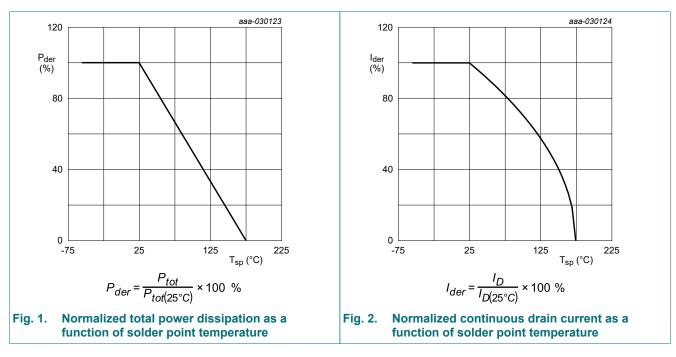
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

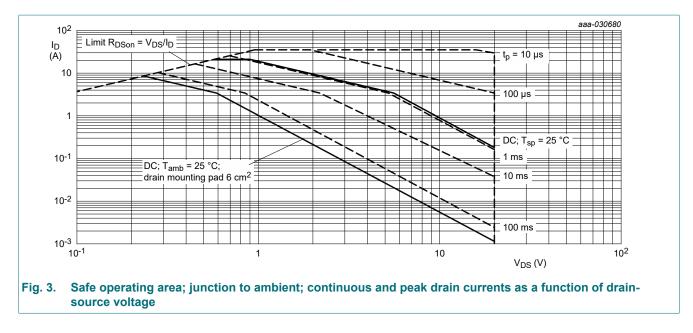
Parameter	Conditions		Min	Мах	Unit
drain-source voltage	T _j = 25 °C		-	20	V
gate-source voltage			-12	12	V
drain current	V _{GS} = 4.5 V; T _{sp} = 25 °C		-	26	А
	V _{GS} = 4.5 V; T _{sp} = 100 °C		-	17	Α
	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	8.5	А
peak drain current	T_{sp} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	106	А
total power dissipation	T _{sp} = 25 °C		-	19	W
	T _{amb} = 25 °C	[1]	-	2	W
junction temperature			-55	175	°C
ambient temperature			-55	175	°C
storage temperature			-65	175	°C
n diode					
source current	T _{sp} = 25 °C		-	19	А
	T _{amb} = 25 °C	[1]	-	2	А
peak source current	single pulse; $t_p \le 10 \ \mu s$; $T_{sp} = 25 \ ^{\circ}C$		-	75	А
Im rating					_
electrostatic discharge voltage	НВМ	[2]	-	2000	V
uggedness		·			
non-repetitive drain- source avalanche energy	T _{j(init)} = 25 °C; I _D = 1.3 A; DUT in v avalanche (unclamped)		-	13	mJ
J	drain-source voltage gate-source voltage drain current peak drain current total power dissipation junction temperature ambient temperature abient temperature storage temperature beak source current peak source current mrating electrostatic discharge voltage ange-tness non-repetitive drain-	$\begin{tabular}{ c c } \hline drain-source voltage & $T_j = 25 \ ^{\circ}C$ \\ \hline gate-source voltage & $V_{GS} = 4.5 \ V; \ T_{sp} = 25 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{sp} = 25 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{amb} = 25 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{amb} = 25 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{amb} = 25 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{amb} = 25 \ ^{\circ}C$ \\ \hline $T_{amb} = $	$\begin{tabular}{ c c c c } \hline \end{tabular} & $T_j = 25\ ^{\circ}C$ & $$$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$$	$\begin{tabular}{ c c c } \hline \mbox{drain-source voltage} & T_j = 25 \ ^{\circ}\ C & -12 \\ \hline \mbox{gate-source voltage} & V_{GS} = 4.5 \ V; \ T_{sp} = 25 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 25 \ ^{\circ}\ C & -12 \\ \hline \mbox{T}_{sp} = 25 \ ^{\circ}\ C & -12 \\ \hline \mbox{T}_{amb} = 25$	$ \begin{array}{ c c c c } \mbox{drain-source voltage} & T_{j} = 25 \ ^{\circ}\ C & -12 & 12 \\ \mbox{gate-source voltage} & V_{GS} = 4.5 \ V; \ T_{sp} = 25 \ ^{\circ}\ C & -26 \\ \hline V_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -17 & 17 \\ \hline V_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -17 & 17 \\ \hline V_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -17 & 17 \\ \hline V_{GS} = 4.5 \ V; \ T_{amb} = 25 \ ^{\circ}\ C & 11 & -2 & 17 \\ \hline V_{GS} = 4.5 \ V; \ T_{amb} = 25 \ ^{\circ}\ C & 11 & -2 & 106 \\ \hline T_{sp} = 25 \ ^{\circ}\ C & 10 \ \mu s & -106 & 19 \\ \hline T_{amb} = 25 \ ^{\circ}\ C & 11 & -2 & 19 \\ \hline T_{amb} = 25 \ ^{\circ}\ C & 11 & -2 & 19 \\ \hline T_{amb} = 25 \ ^{\circ}\ C & -55 & 175 & 175 \\ \hline motion temperature & -55 & 175 & 175 \\ \hline motion temperature & -55 & 175 & 175 \\ \hline motion temperature & -55 & 175 & 175 \\ \hline motion temperature & -665 & 175 & 175 \\ \hline motion temperature & -65 & 175 & 175 \\ \hline motion temperature & -65 & 175 & 175 & 175 \\ \hline motion temperature & -65 & 175 & 175 & 175 \\ \hline motion temperature & -65 & 175 & 1$

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
 Measured between all pins.



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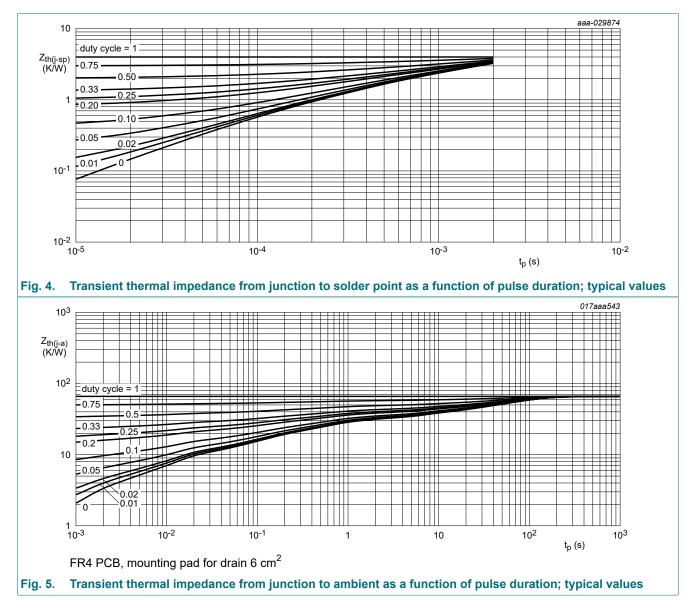
20 V, N-channel Trench MOSFET



9. Thermal characteristics

Table 6. Therma	al characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	66	76	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	4	8	K/W

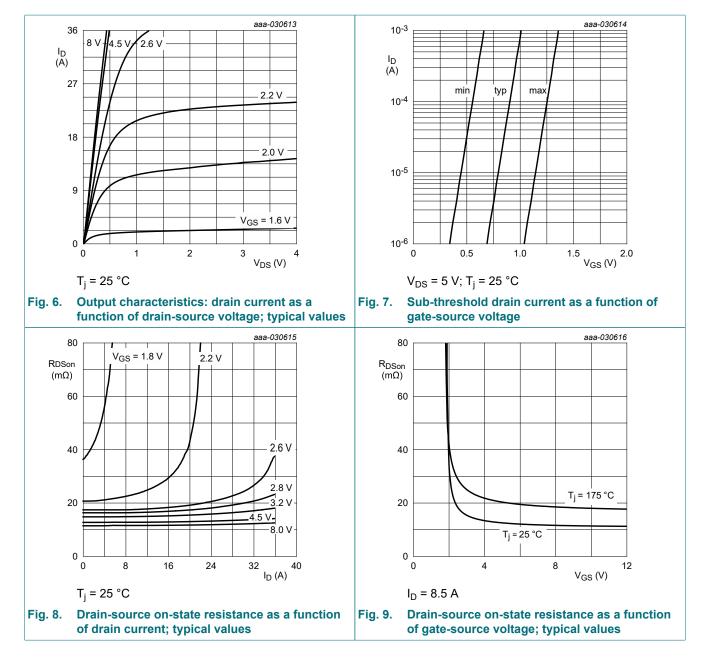
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	20	-	-	V
V _{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}$	0.6	0.95	1.3	V
I _{DSS}	drain leakage current	$V_{DS} = 0 V; V_{GS} = 0 V; T_j = 25 °C$	-	-	1	μA
		V _{DS} = 20 V; V _{GS} = 0 V; T _j = 125 °C	-	-	20	μA
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-2	μA
R _{DSon}	drain-source on-state	V _{GS} = 8 V; I _D = 9 A; T _j = 25 °C	-	11	14	mΩ
	resistance	V _{GS} = 8 V; I _D = 9 A; T _j = 175 °C	-	19	24	mΩ
		V _{GS} = 4.5 V; I _D = 8.5 A; T _j = 25 °C	-	13	16	mΩ
		V _{GS} = 2.5 V; I _D = 3 A; T _j = 25 °C	-	17	21	mΩ
9fs	forward transconductance	V _{DS} = 10 V; I _D = 8.5 A; T _j = 25 °C	-	14.4	-	S
R _G	gate resistance	f = 1 MHz	-	1.4	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I _D = 9 A; V _{GS} = 4.5 V;	-	9.8	15	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.5	-	nC
Q _{GD}	gate-drain charge		-	2.9	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	931	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	144	-	pF
C _{rss}	reverse transfer capacitance		-	121	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; I _D = 9 A; V _{GS} = 4.5 V;	-	4	-	ns
r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	7	-	ns
d(off)	turn-off delay time		-	15	-	ns
l _f	fall time		-	9	-	ns
Source-drai	n diode	· · · · · · · · · · · · · · · · · · ·				
V _{SD}	source-drain voltage	I _S = 2 A; V _{GS} = 0 V; T _j = 25 °C	-	0.7	1.2	V
rr	reverse recovery time	$I_{S} = 2 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	10	-	ns
Q _r	recovered charge	V _{DS} = 10 V; T _j = 25 °C	-	3	-	nC

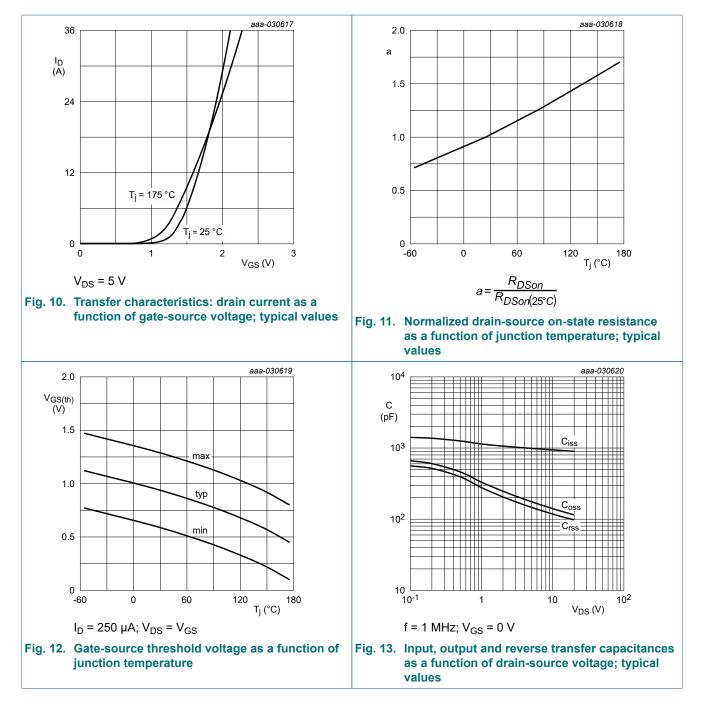
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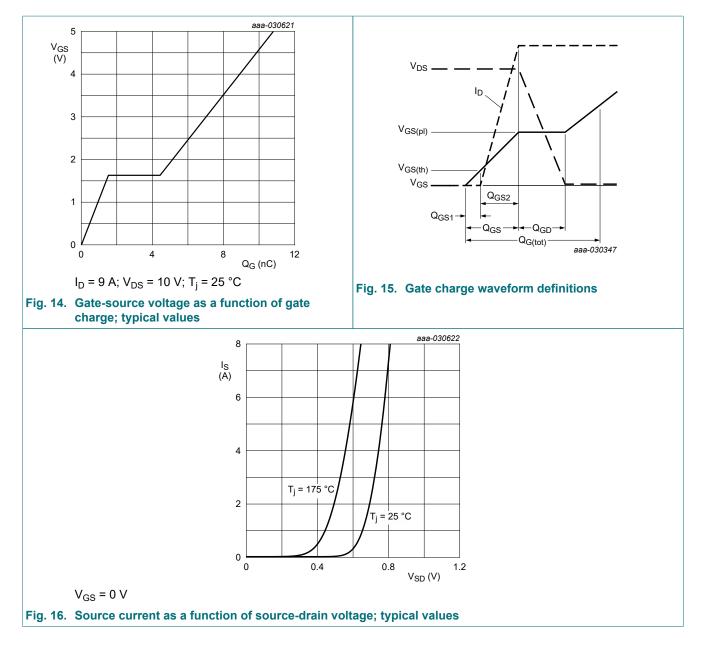
Product data sheet

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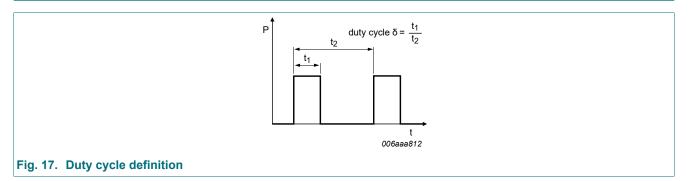
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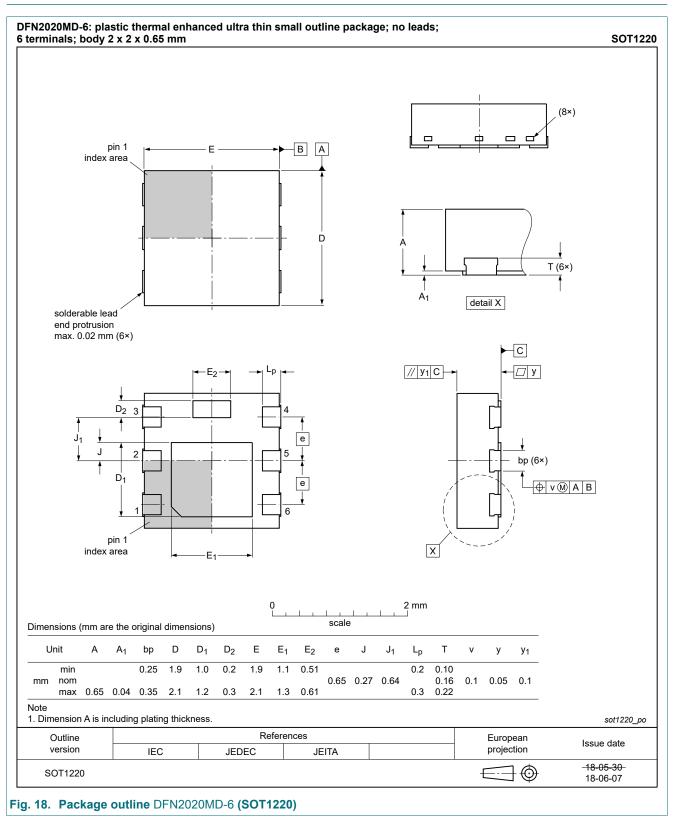
11. Test information



Quality information

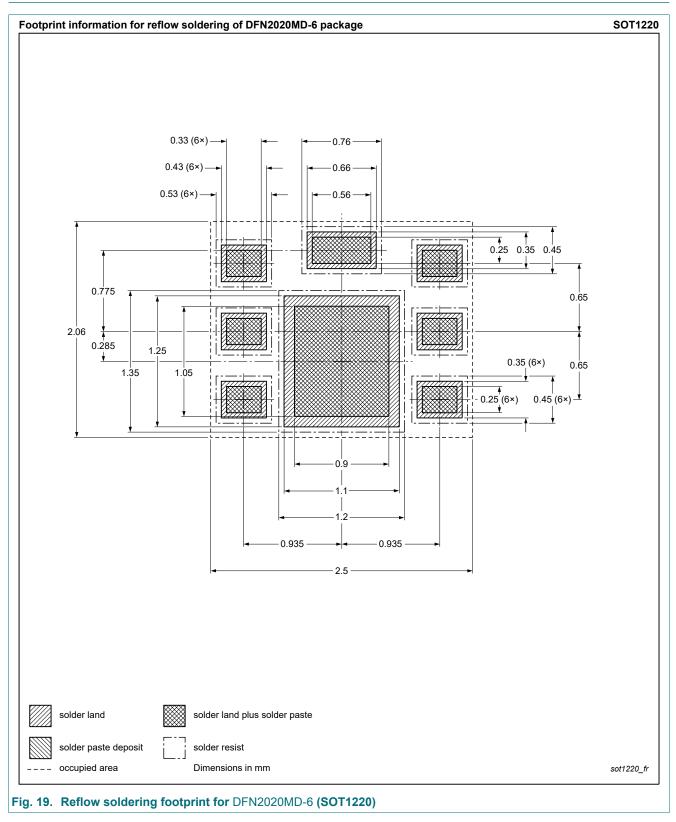
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
BUK4D16-20. v.2	20200709	Product data sheet	-	BUK4D16-20. v.1			
Modifications:	Product status changed.						
BUK4D16-20. v.1	20200114	Objective data sheet	-	-			

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <u>https://www.nexperia.com</u>.

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